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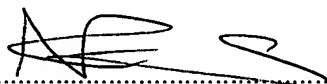
That I am knowledgeable in the English language and in the language in which the below identified international application was filed, and that I believe the English translation of the international application No. PCT/CH2003/000423 is a true and complete translation of the above identified international application as filed.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that wilful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Titel 18 of the United States Code and that such wilful false statements may jeopardize the validity of the application or any patent issued thereon.

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DEC. 31 2004

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CH-8102 OBERENGSTRINGEN

Patent Application for a new Method of Storing Electrical Energy in so called Quantum Batteries

Description

High density storage of electrical energy in a device composed of materials with special electrical properties forming a battery as a “super capacitor” respectively “Quantum Battery” for the usage in stationary as well as mobile applications and also in application where the rapid loading and discharge of energy is required.

1.2. Technical Field

The storage device is independent from a stationary supply source and is therefore utilized to power electrical drives for the mobile traffic (road, train, ship as well as aviation) mainly aimed as energy substitute of fossil fuels. The high density resistance-loss-free storage technology allows also the application in energy supply for household and the transport of energy gained through solar technology. The special materials also allow the manufacture of new types of electronic components. The extreme fast and loss-free discharge of the electrically stored energy make it even possible to use the device also as explosive.

1.3.State of the Technology

The high specific weight when storing electrical energy in conventional batteries and also in capacitors is one of the major shortcoming for the application in mobile traffic. On the other hand the much more advantageous direct storage of chemical energy in fossil fuels and its ease of utilization led to an unacceptable waste of irrecoverable natural reserves. Furthermore the technical storage and discharge of electrical energy in e.g. lead batteries is bound to a high resistance, what results in high heat losses which does strongly limit loading and discharge speeds. The so far available “super capacitors” are functioning on a different physical principle. They operate only

on low voltages, are sensible to mechanical shocks; show some elevated resistances and have several orders of magnitude lower energy and power densities.

1.4. Detailed Description

1.4.1. Advantages

The new device allows to directly store electrical energy with a density in the same order of magnitude as energy can be stored as chemical energy in fossil fuels.

Densities in the range of 1 until over 15 MJ/kg can be reached. The special materials of the new storage device allow nearly unlimited loading and discharging cycles, the material does not wear. During operation the storage device does not show losses due to resistance. The device is proof against any mechanical shock or excessive accelerations as well as extreme temperatures. Also any positioning in space is irrelevant.

1.4.2. Basis of the Invention

The invention is based on the physical effect that very small particles of a strong dipolar crystal material such as TiO_2 (strong electro negativity) embedded in an insulating matrix e.g. SiO_2 or polymer resin and under the stress of a strong electrical field and at a critical voltage (loading condition) are becoming conductive (semiconductor) by means of virtual photon resonance (a new quantum physical effect) and are thus taking up energy which is then stored in a similar way as for a normal plate capacitor. The storage device can be built for voltages from a few volts to thousands of volts. The storage capacity is only limited by the maximum possible physical mechanical dimensions.

1.4.3. Technical Design

The storage crystals such as TiO_2 , SrTiO_3 or similar, either ground to grains of some nm size or as nm-thick layers are applied together with an insulating medium on a carrier surface. There exists particular prerequisite for the type of the crystal, mainly the type "Rutile" is essential.

Two different processes are possible:

- a) A mixture of ground crystals grains and polymer resin are first dispersed and then electrostatically sprayed on a compound film composed of a metal and a polymer foil, which is either continuously put on a flat table or wrapped around a tube-type mandril. The isolated metal foil of the compounded film is the counter electrode. Due to the insulating resin and the compound film the electrical charges when arriving with the wet resin on the surface cannot flow to ground. These charges are building together with the metal foil a very strong electrical field, which exerts by means of the capacitive effect very strong surface forces. These surface forces are causing geometrically exact forms, and in the case of the mandril exact round layers of extreme accurate thickness. Same, due to the strong surface forces also a high hydraulic pressure in the wet resin is applied so that the layers become air pore-free. Additionally the strong electrostatic field causes a proper alignment of the dipoles. The resin is then cured by heat or radiation. Thereafter the layered film is cut and formed into a multi layer capacitor. The cut films can either be arranged flat or wound up. Finally the metallic parts of the device are alternatively electrically connected forming the positive and negative poles of the storage device.
- b) By means of Chemical Vapor Deposition (CVD) or Physical Vapor Deposition (PVD) several thin layers of the storage crystals e.g. TiO_2 are deposited alternatively together with insulation layers e.g. SiO_2 on a planar carrier surface which itself is covered by a conductive material such as e.g. platinum forming the bottom electrode. Through proper annealing at temperature at some 700°C polycrystalline layers are achieved. After deposition of each resonance layer it becomes fully sandwich-type covered by an overlapping insulator layer providing also fixation. Thus after the subsequent annealing process above 800°C for achieving the Rutile phase, when cooling down, the resonance layers do not delaminate even having strongly different thermal expansion coefficients. Finally a metallic cover layer is placed forming the top electrode of the device. It is also possible to deposit several combinations of layers.

Eventually the storage device will be coated by an isolating material and the electrodes connected to external clamps or through strip lines to the control logic.